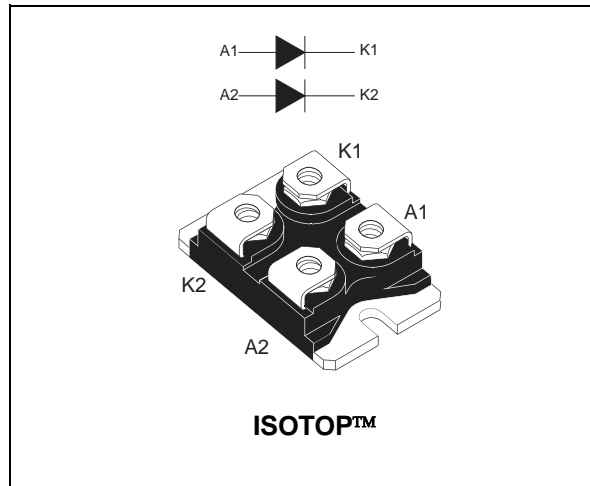




HIGH FREQUENCY SECONDARY RECTIFIER

MAJOR PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 60 A
V_{RRM}	300 V
$T_j (max)$	150 °C
$V_F (max)$	1 V
$t_{rr} (max)$	70 ns



FEATURES AND BENEFITS

- COMBINES HIGHEST RECOVERY AND REVERSE VOLTAGE PERFORMANCE
- ULTRA-FAST, SOFT AND NOISE-FREE RECOVERY
- INSULATED PACKAGE: ISOTOP
Insulated voltage: 2500 V_{RMS}
Capacitance: < 45 pF
- LOW INDUCTANCE AND LOW CAPACITANCE ALLOW SIMPLIFIED LAYOUT

DESCRIPTION

Dual rectifiers suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in ISOTOP, this device is intended for use in low voltage, high frequency inverters, free wheeling operation, welding equipment and telecom power supplies.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		300	V
$I_{F(RMS)}$	RMS forward current		150	A
$I_{F(AV)}$	Average forward current	$T_c = 85^\circ\text{C}$ $\delta = 0.5$	Per diode 120	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ sinusoidal	600	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100 \mu\text{s}$ square	5	A
T_{stg}	Storage temperature range		- 55 to + 150	°C
T_j	Maximum operating junction temperature		150	°C

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STTH12003TV

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.8	$^{\circ}\text{C}/\text{W}$
$R_{th(c)}$		Total	0.45	
	Coupling	0.1		

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode 1}) = P (\text{diode 1}) \times R_{th(j-c)} (\text{per diode}) + P (\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$V_R = 300 \text{ V}$	$T_j = 25^{\circ}\text{C}$			120	μA
			$T_j = 125^{\circ}\text{C}$		0.12	1.2	mA
V_F^{**}	Forward voltage drop	$I_F = 60 \text{ A}$	$T_j = 25^{\circ}\text{C}$			1.25	V
			$T_j = 125^{\circ}\text{C}$		0.85	1	

Pulse test : * $t_p = 5 \text{ ms}$, $\delta < 2 \%$

** $t_p = 380 \mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation:

$$P = 0.75 \times I_{F(AV)} + 0.0042 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Tests conditions			Min.	Typ.	Max.	Unit
trr	$I_F = 0.5 \text{ A}$	$I_{rr} = 0.25 \text{ A}$	$I_R = 1 \text{ A}$	$T_j = 25^{\circ}\text{C}$		55	ns
	$I_F = 1 \text{ A}$	$di_F/dt = -50 \text{ A}/\mu\text{s}$	$V_R = 30 \text{ V}$	$T_j = 25^{\circ}\text{C}$		70	
tfr	$I_F = 60 \text{ A}$	$di_F/dt = 200 \text{ A}/\mu\text{s}$		$T_j = 25^{\circ}\text{C}$		600	ns
V_{FP}	$V_{FR} = 1.1 \times V_F \text{ max.}$			$T_j = 25^{\circ}\text{C}$		5	V
S_{factor}	$V_{CC} = 200 \text{ V}$	$I_F = 60 \text{ A}$		$T_j = 125^{\circ}\text{C}$	0.3		-
I_{RM}	$di_F/dt = 200 \text{ A}/\mu\text{s}$						14

Fig. 1: Conduction losses versus average current (per diode).

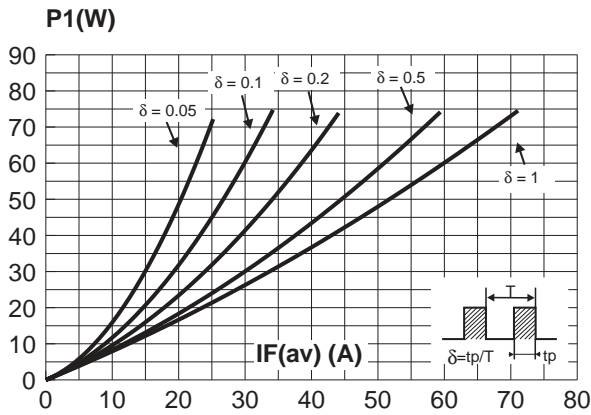


Fig. 2: Forward voltage drop versus forward current (per diode).

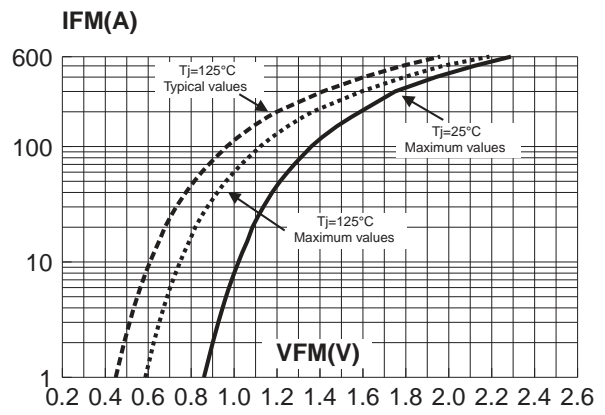


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

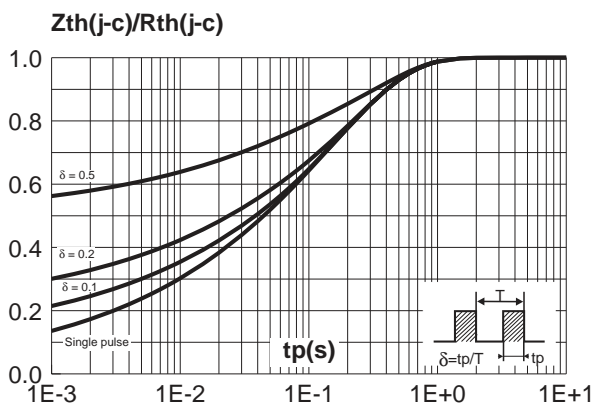


Fig. 4: Peak reverse recovery current versus dI_F/dt (90% confidence, per diode).

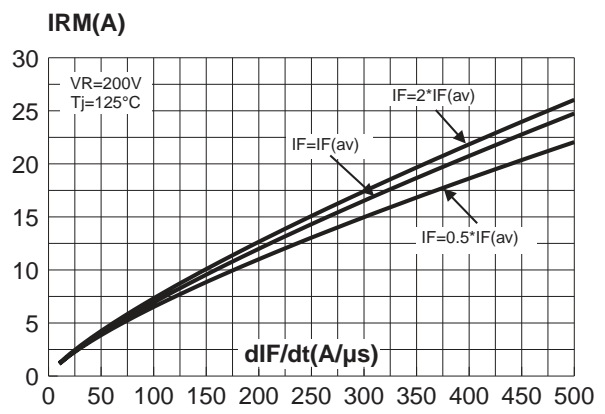


Fig. 5: Reverse recovery time versus dI_F/dt (90% confidence, per diode).

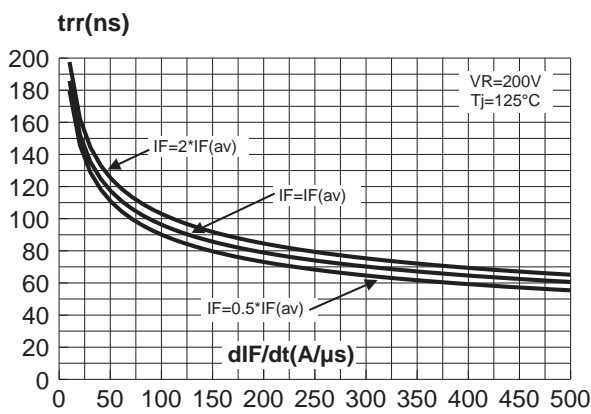


Fig. 6: Softness factor (tb/ta) versus dI_F/dt (typical values, per diode).

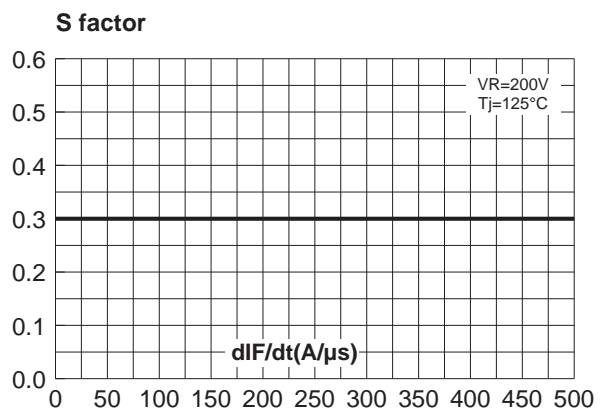


Fig. 7: Relative variation of dynamic parameters versus junction temperature (reference: $T_j = 125^\circ\text{C}$).

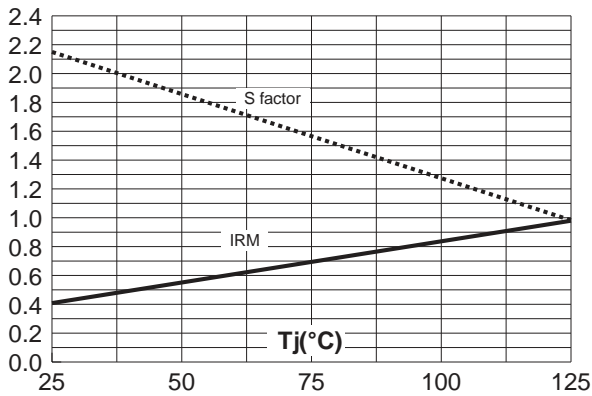


Fig. 8: Transient peak forward voltage versus dI_F/dt (90% confidence, per diode).

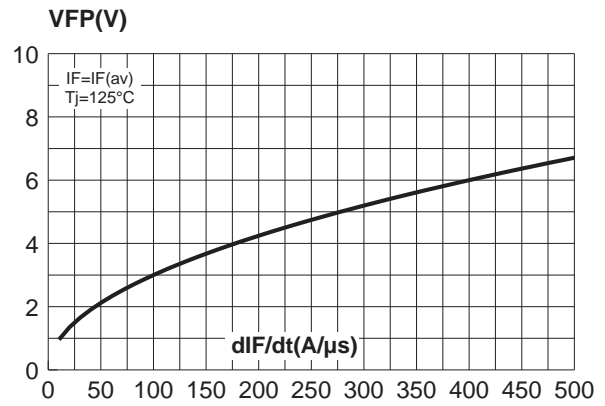
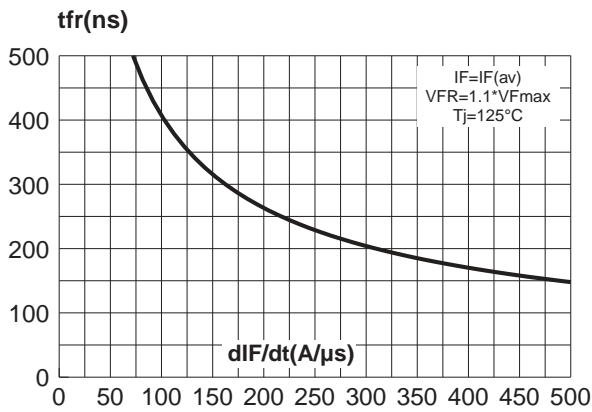
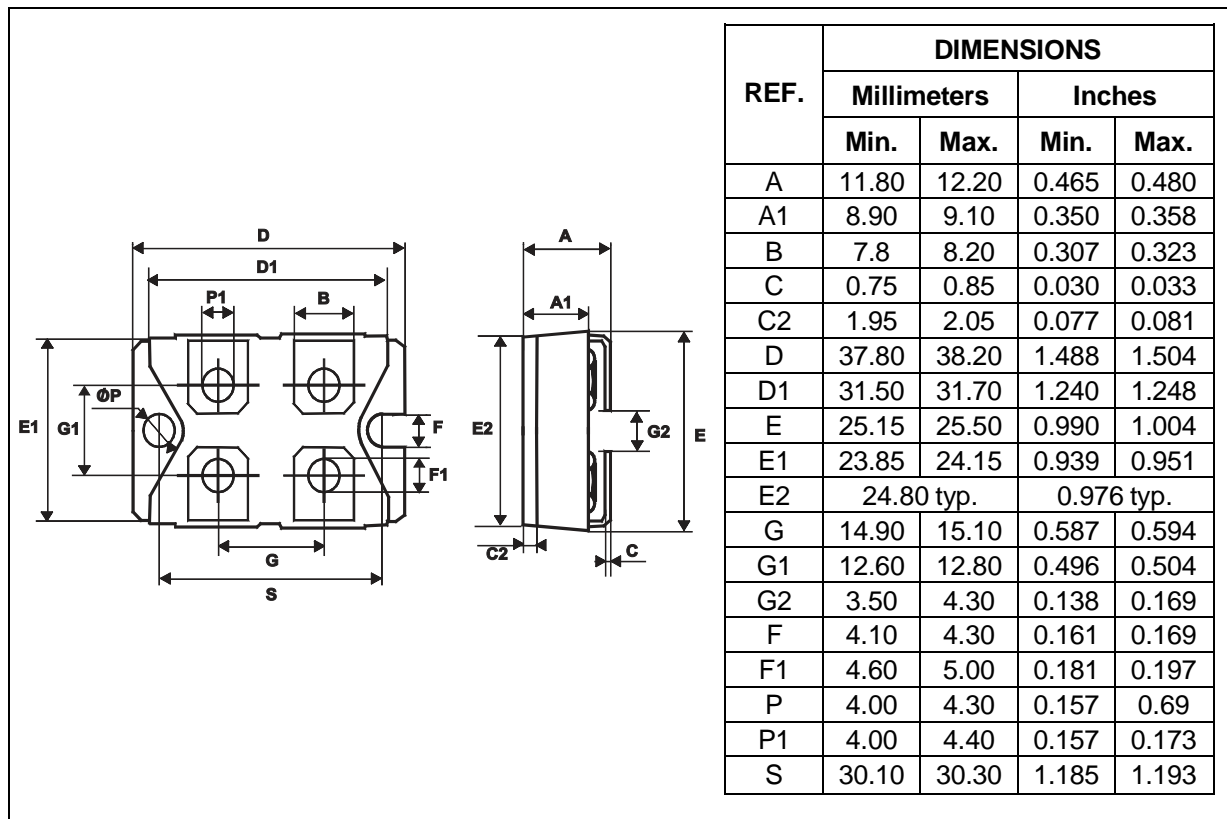


Fig. 9: Forward recovery time versus dI_F/dt (90% confidence, per diode).



PACKAGE MECHANICAL DATA
 ISOTOP


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Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH12003TV1	STTH12003TV	ISOTOP	27g without screws	10 with screws	Tube

- Cooling method: by conduction (C)
- Recommended torque value: 1.3 N.m.
- Maximum torque value: 1.5 N.m.
- Epoxy meets UL 94,V0

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